



# BUK7Y10-30B,115 Information



For Reference Only

**Part Number** BUK7Y10-30B,115 **Manufacturer** Nexperia USA Inc.

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 30V 67A LFPAK

Package SC-100, SOT-669

For the pricing/inventory/lead time, please contact

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# **BUK7Y10-30B,115 Specifications**

Manufacturer Part NumberBUK7Y10-30B,115ManufacturerNexperia USA Inc.CategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageSC-100, SOT-669SeriesAutomotive, AEC-Q101, TrenchMOS?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C67A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 1mAGate Charge (Qg) (Max) @ Vgs18.8nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1183pF @ 25VVgs (Max)±20VFET Feature-		
Category  Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single  Sc-100, SOT-669  Series  Automotive, AEC-Q101, TrenchMOS?  FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  Discrete Semiconductor Products  Transistors - FETs, MOSFETs - Single  SC-100, SOT-669  Automotive, AEC-Q101, TrenchMOS?  N-Channel  MOSFET (Metal Oxide)  50V  67A (Tc)  10V  11V  Vgs(th) (Max) @ Id  4V @ 1mA  Gate Charge (Qg) (Max) @ Vgs  18.8nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)	Manufacturer Part Number	BUK7Y10-30B,115
Transistors - FETs, MOSFETs - Single  Package SC-100, SOT-669 Series Automotive, AEC-Q101, TrenchMOS?  FET Type N-Channel Technology MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max)  Transistors - FETs, MOSFETs - Single SC-100, SOT-669  Automotive, AEC-Q101, TrenchMOS?  N-Channel  10V  MOSFET (Metal Oxide)  10V  4V @ 1mA  1183pF @ 25V  Vgs (Max)	Manufacturer	Nexperia USA Inc.
Package         SC-100, SOT-669           Series         Automotive, AEC-Q101, TrenchMOS?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         30V           Current - Continuous Drain (Id) @ 25°C         67A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 1mA           Gate Charge (Qg) (Max) @ Vgs         18.8nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1183pF @ 25V           Vgs (Max)         ±20V	Category	Discrete Semiconductor Products
Series Automotive, AEC-Q101, TrenchMOS?  FET Type N-Channel Technology MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss) 30V  Current - Continuous Drain (Id) @ 25°C 67A (Tc)  Drive Voltage (Max Rds On, Min Rds On) 10V  Vgs(th) (Max) @ Id 4V @ 1mA  Gate Charge (Qg) (Max) @ Vgs 18.8nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds 1183pF @ 25V  Vgs (Max) ±20V		Transistors - FETs, MOSFETs - Single
FET Type  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  Vgs (Max)  N-Channel  N-Channel  N-Channel  N-Channel  N-Channel  N-Channel  10V  10V  1180  1180  1180  1183	Package	SC-100, SOT-669
Technology  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  67A (Tc)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ### MOSFET (Metal Oxide)  ### A00	Series	Automotive, AEC-Q101, TrenchMOS?
Drain to Source Voltage (Vdss)       30V         Current - Continuous Drain (Id) @ 25°C       67A (Tc)         Drive Voltage (Max Rds On, Min Rds On)       10V         Vgs(th) (Max) @ Id       4V @ 1mA         Gate Charge (Qg) (Max) @ Vgs       18.8nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       1183pF @ 25V         Vgs (Max)       ±20V	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C       67A (Tc)         Drive Voltage (Max Rds On, Min Rds On)       10V         Vgs(th) (Max) @ Id       4V @ 1mA         Gate Charge (Qg) (Max) @ Vgs       18.8nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       1183pF @ 25V         Vgs (Max)       ±20V	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)       10V         Vgs(th) (Max) @ Id       4V @ 1mA         Gate Charge (Qg) (Max) @ Vgs       18.8nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       1183pF @ 25V         Vgs (Max)       ±20V	Drain to Source Voltage (Vdss)	30V
Vgs(th) (Max) @ Id       4V @ 1mA         Gate Charge (Qg) (Max) @ Vgs       18.8nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       1183pF @ 25V         Vgs (Max)       ±20V	Current - Continuous Drain (Id) @ 25°C	67A (Tc)
Gate Charge (Qg) (Max) @ Vgs       18.8nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       1183pF @ 25V         Vgs (Max)       ±20V	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds	Vgs(th) (Max) @ Id	4V @ 1mA
Vgs (Max) ±20V	Gate Charge (Qg) (Max) @ Vgs	18.8nC @ 10V
	Input Capacitance (Ciss) (Max) @ Vds	1183pF @ 25V
FET Feature -	Vgs (Max)	±20V
	FET Feature	-
Power Dissipation (Max) 85W (Tc)	Power Dissipation (Max)	85W (Tc)
Rds On (Max) @ Id, Vgs 10 mOhm @ 25A, 10V	Rds On (Max) @ Id, Vgs	10 mOhm @ 25A, 10V
Operating Temperature $-55^{\circ}\text{C} \sim 175^{\circ}\text{C} \text{ (TJ)}$	Operating Temperature	-55°C ~ 175°C (TJ)
Mounting Type Surface Mount	Mounting Type	Surface Mount
Supplier Device Package LFPAK56, Power-SO8	Supplier Device Package	LFPAK56, Power-SO8
Package / Case SC-100, SOT-669	Package / Case	SC-100, SOT-669
Report errors'		Report errors?

### BUK7Y10-30B,115 Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### **BUK7Y10-30B,115 Payment Methods**



















## **BUK7Y10-30B,115 Shipping Methods**













If you have any question about BUK7Y10-30B,115, please do not hesitate to contact us!

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